

SEMITOP[®] 3

IGBT Module

SK15GD126ET

Preliminary Data

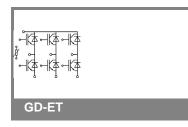
Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Inverter

 $T_s = 25 \text{ °C}$, unless otherwise specified **Absolute Maximum Ratings** Symbol Conditions Values Units IGBT V_{CES} T_i = 25 °C 1200 V T_i = 150 °C T_e = 25 °C 22 А Ι_C T_s = 80 °C 15 А 30 А I_{CRM}= 2 x I_{Cnom} I_{CRM} ± 20 V V_{GES} V_{CC} = 600 V; $V_{GE} \le 20$ V; T_i = 125 °C 10 μs t_{psc} VCES < 1200 V Inverse Diode T_i = 150 °C T_s = 25 °C 25 А I_F T_s = 80 °C 17 А I_{FRM}= 2 x I_{Fnom} 30 А I_{FRM} Module А I_{t(RMS)} T_{vj} -40 ... +150 °C T_{stg} -40 ... +125 °C 2500 V V_{isol} AC, 1 min. T_s = 25 °C, unless otherwise specified **Characteristics** Symbol Conditions min. max. Units typ. IGBT V_{GE(th)} $V_{GE} = V_{CE}, I_C = 0.6 \text{ mA}$ $V_{GE} = 0 \text{ V}, V_{CE} = V_{CES}$ 5 5,8 6,5 V 0,1 T_i = 25 °C mΑ ICES T_i = 125 °C mΑ V_{CE} = 0 V, V_{GE} = 20 V T_i = 25 °C 120 nA IGES T_i = 125 °C nA T_i = 25 °C V V_{CE0} 1 1,2 V T_i = 125 °C 0,9 T_i = 25°C V_{GE} = 15 V 47 60 mΩ r_{CE} T_i = 125°C 73 mΩ I_{Cnom} = 15 A, V_{GE} = 15 V 1,7 2,1 ٧ V_{CE(sat)} T_j = 25°C_{chiplev}. T_i = 125°C_{chipley} 2,2 V Cies 1.1 nF V_{CE} = 25, V_{GE} = 0 V f = 1 MHz 0,058 C_{oes} nF 0,048 C_{res} nF 85 ns t_{d(on)} $R_{Gon} = 40 \Omega$ V_{CC} = 600V 30 ns E_{on} I_C= 15A 2 mJ $R_{Goff} = 40 \Omega$ T_i = 125 °C 430 t_{d(off)} ns V_{GE}=±15V 90 ns t,



per IGBT

 $\mathsf{E}_{\mathsf{off}}$

R_{th(j-s)}

mJ

K/W

1,6

1,8



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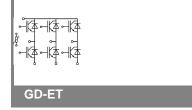
Typical Applications*

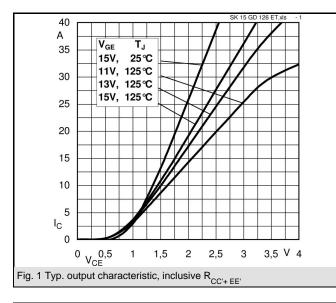
Inverter

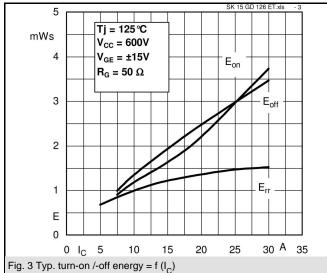
Symbol	Conditions	1	min	4 100	mov	Unite
-	Conditions		min.	typ.	max.	Units
Inverse [
$V_F = V_{EC}$	I _{Fnom} = 15 A; V _{GE} = 0 V			1,6	1,8	V
		T _j = 125 °C _{chiplev.}		1,6		V
V _{F0}		T _j = 25 °C		1	1,1	V
		T _j = 125 °C		0,8		V
r _F		T _j = 25 °C		40	47	mΩ
		T _j = 125 °C		53		mΩ
I _{RRM}	I _F = 15 A	T _i = 125 °C		21		Α
Q _{rr}	di/dt = -570 A/µs	2		3,5		μC
E _{rr}	V _{CC} = 600V			1,4		mJ
R _{th(j-s)D}	per diode				2,1	K/W
M _s	to heat sink		2,25		2,5	Nm
w				30		g
Tempera	ture sensor					
R ₁₀₀	T _s =100°C (R ₂₅ =5kΩ)			493±5%		Ω

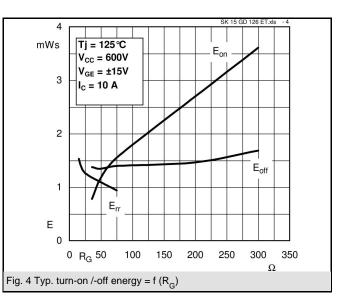
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

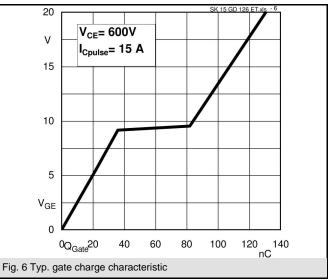
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.





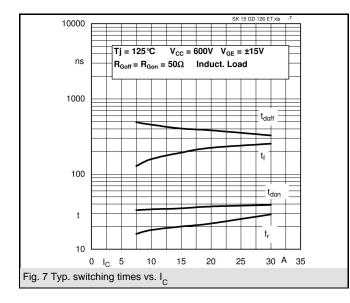


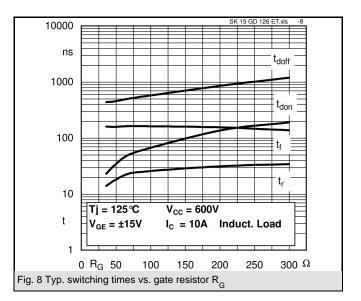


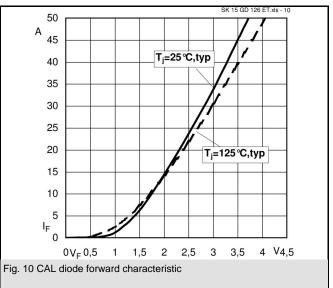


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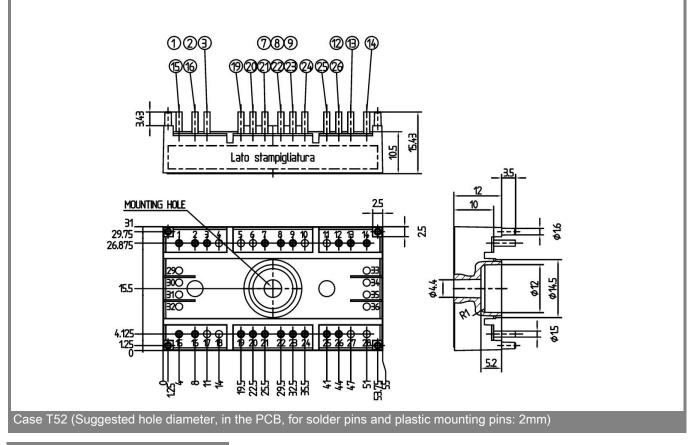
21-02-2007 SCT

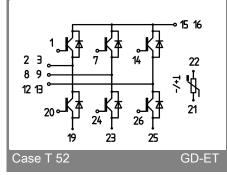






UL recognized file





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